Preferred Devices

Thyristor Surge Protectors High Voltage Bidirectional TSPD

These Thyristor Surge Protective devices (TSPD) prevent overvoltage damage to sensitive circuits by lightning, induction and power line crossings. They are breakover-triggered crowbar protectors. Turn-off occurs when the surge current falls below the holding current value.

Secondary protection applications for electronic telecom equipment at customer premises.

Features

- High Surge Current Capability: 50 A 10 x 1000 µsec, for Controlled Temperature Environments
- The MMT05B230T3 Series is used to help equipment meet various regulatory requirements including: Bellcore 1089, ITU K.20 & K.21, IEC 950, UL 1459 & 1950 and FCC Part 68
- Bidirectional Protection in a Single Device
- Little Change of Voltage Limit with Transient Amplitude or Rate
- Freedom from Wearout Mechanisms Present in Non–Semiconductor Devices
- Fail–Safe, Shorts When Overstressed, Preventing Continued Unprotected Operation
- Surface Mount Technology (SMT)
- 🔊 Indicates UL Registered File #E210057
- Pb–Free Packages are Available

MAXIMUM RATINGS (T_J = $25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Off-State Voltage – Maximum MMT05B230T3 MMT05B260T3 MMT05B310T3	V _{DM}	$^{\pm}_{\pm}200 \\ ^{\pm}270$	V
Maximum Pulse Surge Short Circuit Current Non–Repetitive Double Exponential Decay Waveform (Notes 1 and 2) (–25°C Initial Temperature) 8 x 20 μsec 10 x 160 μsec 10 x 560 μsec 10 x 1000 μsec	IPPS1 IPPS2 IPPS3 IPPS4	$^{\pm 150}_{\pm 100}_{\pm 70}_{\pm 50}$	A(pk)
$\begin{array}{l} \mbox{Maximum Non-Repetitive Rate of Change of} \\ \mbox{On-State Current Double Exponential Waveform,} \\ \mbox{R} = 1.0, \ \mbox{L} = 1.5 \ \mbox{μH}, \ \mbox{C} = 1.67 \ \mbox{μF}, \ \mbox{I_{pk}} = 110 \ \mbox{Max} \end{array}$	di/dt	±150	A/μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Allow cooling before testing second polarity.

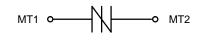
2. Measured under pulse conditions to reduce heating.



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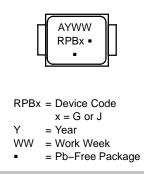
BIDIRECTIONAL TSPD (%) 50 AMPERE SURGE 265 thru 365 VOLTS





SMB (No Polarity) (Essentially JEDEC DO-214AA) CASE 403C

MARKING DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Operating Temperature Range Blocking or Conducting State	T _{J1}	-40 to +125	°C
Overload Junction Temperature – Maximum Conducting State Only	T _{J2}	+175	°C
Instantaneous Peak Power Dissipation (I _{pk} = 50 A, 10x1000 μ sec @ 25°C)	P _{PK}	2000	W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	ΤL	260	°C

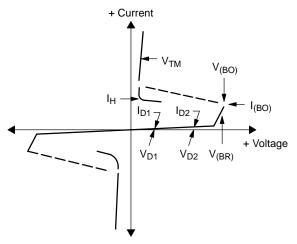
ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted) Devices are bidirectional. All electrical parameters apply to forward and reverse polarities.

Characteristics	Symbol	Min	Тур	Max	Unit	
Breakover Voltage (Both polarities) (dv/dt = 100 V/ μ s, I _{SC} = 1.0 A, Vdc = 1000 V) (+65°C)	MMT05B230T3 MMT05B260T3 MMT05B310T3 MMT05B230T3	V _(BO)	- - -	- - -	265 320 365 280	V
	MMT05B260T3 MMT05B310T3		_	_	340 400	
Breakover Voltage (Both polarities) (f = 60 Hz, I_{SC} = 1.0 A(rms), V_{OC} = 1000 V(rms), R_I = 1.0 k Ω , t = 0.5 cycle) (Note 3) (+65°C)	MMT05B230T3 MMT05B260T3 MMT05B310T3	V _(BO)	- - -	- - -	265 320 365	V
	MMT05B230T3 MMT05B260T3 MMT05B310T3		- - -	- - -	280 340 400	
Breakover Voltage Temperature Coefficient		dV _(BO) /dT _J	-	0.08	-	%/°C
Breakdown Voltage ($I_{(BR)}$ = 1.0 mA) Both polarities	MMT05B230T3 MMT05B260T3 MMT05B310T3	V _(BR)	_ _ _	190 240 280	- - -	V
Off State Current (V_{D1} = 50 V) Both polarities (V_{D2} = V_{DM}) Both polarities		I _{D1} I _{D2}	-		2.0 5.0	μΑ
On–State Voltage (I _T = 1.0 A) (PW \leq 300 μ s, Duty Cycle \leq 2%) (Note 3)		V _T	-	1.53	3.0	V
Breakover Current (f = 60 Hz, V_{DM} = 1000 V(rms), R _S = 1.0	I _{BO}	-	230	-	mA	
Holding Current (Both polarities) (Note 3) $V_S = 500 \text{ V}; I_T \text{ (Initiating Current)} = \pm 1.0 \text{ A}$		I _H	150	340	-	mA
Critical Rate of Rise of Off–State Voltage (Linear waveform, V_D = Rated V_{BR} , T_J = 25°C)		dv/dt	2000	-	-	V/µs
Capacitance (f = 1.0 MHz, 50 Vdc, 1.0 V rms Signal) (f = 1.0 MHz, 2.0 Vdc, 15 mV rms Signal)		Co	- -	22 53	- 75	pF

3. Measured under pulse conditions to reduce heating.

Voltage Current Characteristic of TSPD (Bidirectional Device)

Symbol	Parameter
I _{D1} , I _{D2}	Off State Leakage Current
V _{D1} , V _{D2}	Off State Blocking Voltage
V _{BR}	Breakdown Voltage
V _{BO}	Breakover Voltage
I _{BO}	Breakover Current
I _H	Holding Current
V _{TM}	On State Voltage



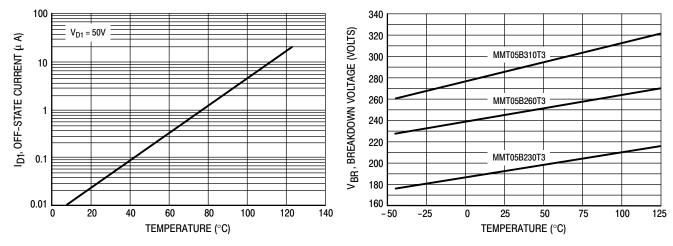


Figure 1. Off-State Current versus Temperature

Figure 2. Breakdown Voltage versus Temperature

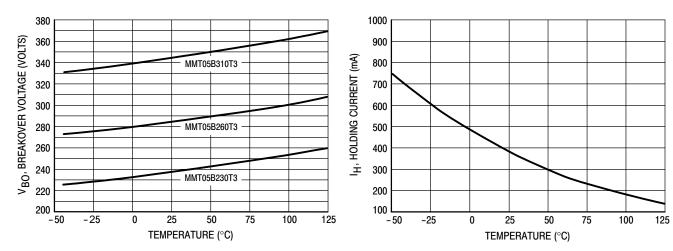


Figure 3. Breakover Voltage versus Temperature

Figure 4. Holding Current versus Temperature

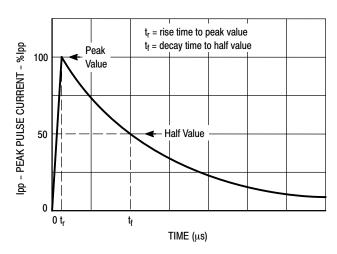


Figure 5. Exponential Decay Pulse Waveform

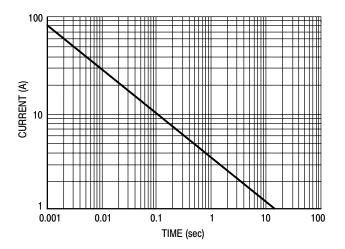
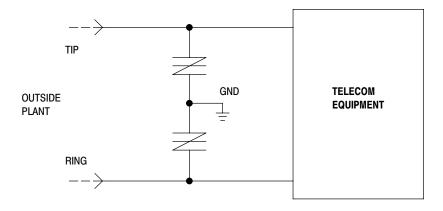
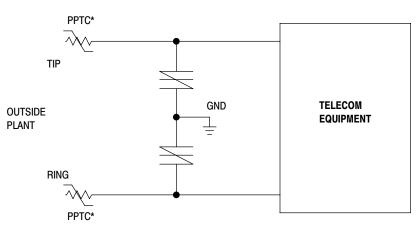
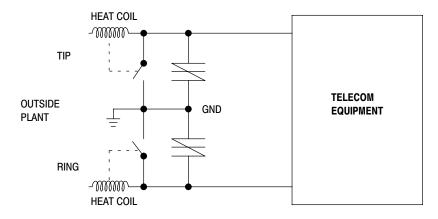


Figure 6. Peak Surge On–State Current versus Surge Current Duration, Sinusoidal Waveform





*Polymeric PTC (positive temperature coefficient) overcurrent protection device



ORDERING INFORMATION

Device	Package	Shipping [†]
MMT05B230T3	SMB	
MMT05B230T3G	SMB (Pb-Free)	
MMT05B260T3	SMB	
MMT05B260T3G	SMB (Pb-Free)	2500 / Tape & Reel
MMT05B310T3	SMB	
MMT05B310T3G	SMB (Pb-Free)	

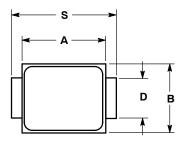
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

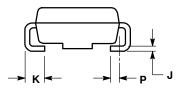


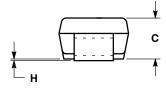
SMB CASE 403C-01 **ISSUE A**

DATE 01/02/2000









NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.160	0.180	4.06	4.57
В	0.130	0.150	3.30	3.81
С	0.075	0.095	1.90	2.41
D	0.077	0.083	1.96	2.11
Н	0.0020	0.0060	0.051	0.152
J	0.006	0.012	0.15	0.30
Κ	0.030	0.050	0.76	1.27
Р	0.020 REF		0.51 REF	
S	0.205	0.220	5.21	5.59

MARKING DIAGRAM



= Specific Device Code XXXX Υ = Year WW = Work Week

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